

TO SEPARATE, HOLD TOP AND BOTTOM EDGES, SNAP-APART AND DISCARD CARBON

FORM PTO-892
(REV. 2-92)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

NOTICE OF REFERENCES CITED

SERIAL NO. 08/462742

GROUP/UNIT 1104

ATTACHMENT TO PAPER NUMBER 5

APPLICANT(S) ZHANG et al.

U.S. PATENT DOCUMENTS				CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
DOCUMENT NO.	DATE	NAME				
A 5278093	1/11/94	YONEHARA	437	109	9/24/90	
B 4394191	7/6/83	WADA et al.	—	—		
C 4309224	1/5/82	SHIBATA	437	40 TET	6/23/92	
D 5264383	11/23/93	YOUNG	437	233		
E RE33321	9/4/90	MAGARINO et al.	437	99		
F 4534820	8/13/85	MORI et al.	437	233	8/8/91	
G 5318661	6/7/94	KUMONAI	437	174	12/3/93	
H 5403772	4/4/95	ZHANG et al.	437	21	6/29/93	
I 5387530	2/7/95	DOYLE et al.	437	159		
J 3783049	1/1/74	SANDERA	437	159		
K 3988762	10/26/76	Cline et al.	437	159		

FOREIGN PATENT DOCUMENTS				CLASS	SUB-CLASS	PERTINENT SMTS. DWG.	P. SPEC.
DOCUMENT NO.	DATE	COUNTRY	NAME				
L 55-162224	12/17/80	JAPAN	SHIBATA	437	40 TET		
M 2171844	9/3/86	U.K.	Scovell et al.	437	109		
N 2-52419	2/22/90	JAPAN	TAJIMA	437	109		
O 2-27320	1/30/90	JAPAN	AOYAMA et al.	437	40 TET		
P 2-137326	5/25/90	JAPAN	OKABAYASHI	—	—		
Q							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

- R O. SCHOENFELD, et al., J. PHYS. CHEM. SOLIDS, 56, 1 (1995) 123
- S "Microcrystalline composite Si-NiSi₂ Thin Films"
- T O. SCHOENFELD, et al., Thin Solid Films, 261 (1995) 236
- U "Crystallization of α-Si by NiSi₂ precipitates"
- A.V. KUZNETSOV, et al., Nucl. Instr. & Meth. Phys. Res. B 96 (1995) 261 "Solid phase epitaxy of α-Si: Ni"

EXAMINER L RADOMSKY

DATE 10/6/95

* A copy of this reference is not being furnished with this office action.
(See Manual of Patent Examining Procedure, section 707.05 (a).)